

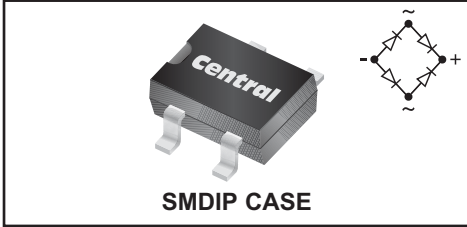
CBRSDSH2-40
SURFACE MOUNT
2 AMP SILICON
SCHOTTKY BRIDGE RECTIFIER



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CBRSDSH2-40 is a full wave bridge rectifier mounted in a durable epoxy surface mount case, utilizing glass passivated chips.



MARKING: FULL PART NUMBER

FEATURES:

- Low Leakage Current (40 μ A TYP @ V_{RRM})
- High 2.0A Current Rating
- Low V_F Schottky Diodes (400mV TYP @ $I_F=2.0A$)

MAXIMUM RATINGS: ($T_A=25^\circ C$)

Peak Repetitive Reverse Voltage	V_{RRM}	40	V
DC Blocking Voltage	V_R	40	V
RMS Reverse Voltage	$V_{R(RMS)}$	28	V
Average Forward Current	I_O	2.0	A
Peak Forward Surge Current (8.3ms)	I_{FSM}	110	A
Operating and Storage Junction Temperature	T_J, T_{stg}	-50 to +125	$^\circ C$
Typical Thermal Resistance (Note 1)	θ_{JA}	40	$^\circ C/W$
Typical Thermal Resistance	θ_{JL}	15	$^\circ C/W$

SYMBOL

V_{RRM}	40	V
V_R	40	V
$V_{R(RMS)}$	28	V
I_O	2.0	A
I_{FSM}	110	A
T_J, T_{stg}	-50 to +125	$^\circ C$
θ_{JA}	40	$^\circ C/W$
θ_{JL}	15	$^\circ C/W$

UNITS

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^\circ C$ unless otherwise noted)

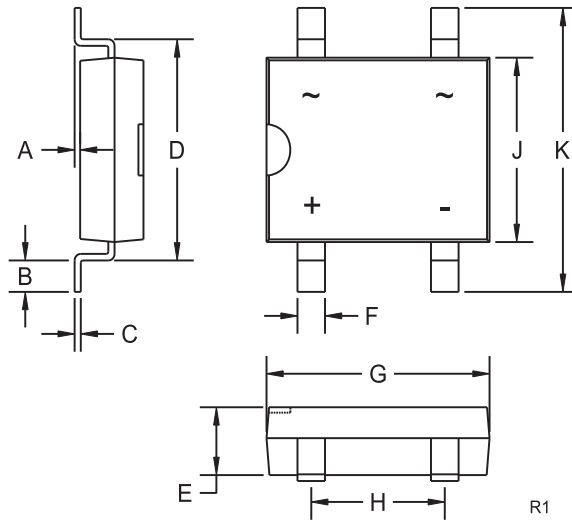
SYMBOL	TEST CONDITIONS	TYP	MAX	UNITS
I_R	$V_R=40V$	40	70	μA
V_F	$I_F=2.0A$	400	450	mV
C_J	$V_R=4.0V, f=1.0MHz$	400	500	pF

Notes: (1) Devices mounted on PCB with 13mm x 13mm copper pads.

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SMDIP CASE - MECHANICAL OUTLINE



DIMENSIONS				
SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.008	0.10	0.20
B	0.040	0.060	1.02	1.52
C	0.009		0.23	
D	0.290	0.310	7.37	7.87
E	0.086	0.098	2.18	2.49
F	0.038	0.042	0.97	1.07
G	0.316	0.335	8.03	8.51
H	0.195	0.205	4.95	5.21
J	0.245	0.255	6.22	6.48
K	0.360	0.410	9.14	10.41

SMDIP (REV: R1)

MARKING: FULL PART NUMBER

R1 (26-October 2011)

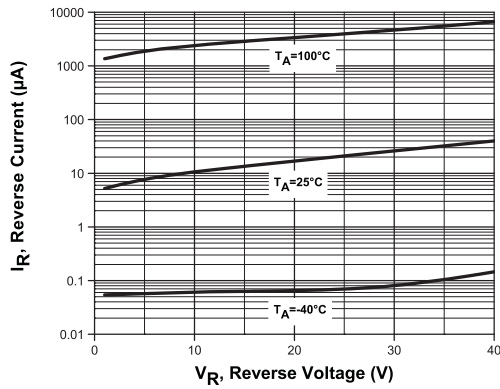
CBRSDSH2-40



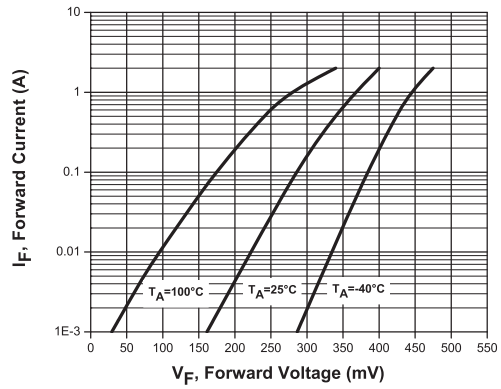
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TYPICAL ELECTRICAL CHARACTERISTICS

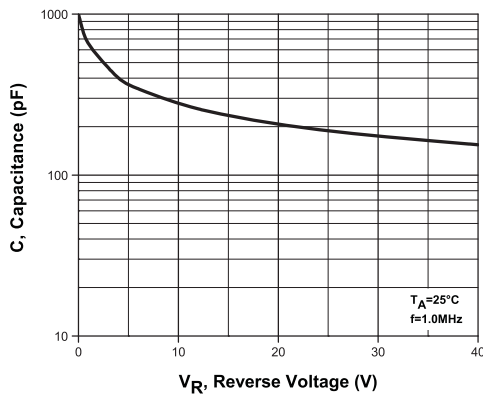
Typical Per Diode Leakage Current



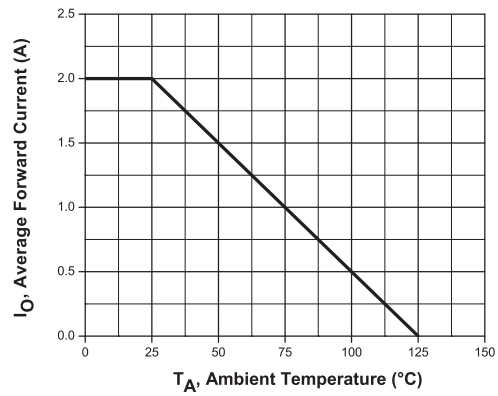
Typical Per Diode Forward Voltage



Typical Per Diode Capacitance



Per Diode Current Derating



R1 (26-October 2011)